

# NPN SILICON RF TRANSISTOR

**DESCRIPTION:**

The **ASI MRF962** is designed for Low-to-medium power amplifier applications, requiring high gain, low noise figure, and low intermodulation distortion.

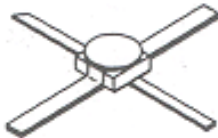
**FEATURES:**

- **NF** = 2.0 dB
- **Omnigold™** Metalization System
- Hermetic stripline, ceramic package

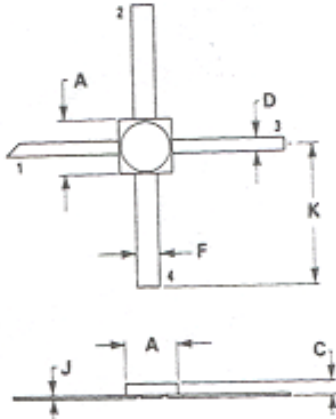
**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	100 mA
<b>V<sub>CB</sub></b>	20 V
<b>P<sub>DISS</sub></b>	.75 W @ T <sub>C</sub> = 100 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	133 °C/W

**PACKAGE STYLE**



DIM	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	2.29	2.67	0.090	0.105
C	0.89	1.40	0.035	0.055
D	0.41	0.61	0.016	0.024
F	0.89	1.09	0.035	0.043
G	0.08	0.15	0.003	0.006
K	4.45	5.84	0.175	0.230



1 = COLLECTOR  
 2 = EMITTER  
 3 = BASE  
 4 = EMITTER

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 1.0 mA		15			<b>V</b>
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 100 μA		20			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 100 μA		3.0			<b>V</b>
<b>I<sub>CBO</sub></b>	V <sub>CB</sub> = 10 V				100	<b>nA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 10 V	I <sub>C</sub> = 50 mA	30		200	<b>---</b>
<b>C<sub>CB</sub></b>	V <sub>CB</sub> = 10 V	f = 1.0 MHz		1.2	1.5	<b>pF</b>
<b>f<sub>t</sub></b>	V <sub>CE</sub> = 10 V	I <sub>C</sub> = 50 mA		4.5		<b>GHz</b>
<b>NF</b>	V <sub>CE</sub> = 10 V	I <sub>C</sub> = 10 mA		2.0		<b>dB</b>